

AVALANCHE ENERGY AND dv/dt RATED HEXFET® TRANSISTOR

IRH9230 P-CHANNEL RAD HARD

-200 Volt, 0.8 Ω , RAD HARD HEXFET

International Rectifier's P-Channel RAD HARD technology HEXFETs demonstrate excellent threshold voltage stability and breakdown voltage stability at total radiation doses as high as 10^5 Rads (Si). Under **identical** pre- and post-radiation test conditions, International Rectifier's P-Channel RAD HARD HEXFETs retain **identical** electrical specifications up to 1×10^5 Rads (Si) total dose. No compensation in gate drive circuitry is required. These devices are also capable of surviving transient ionization pulses as high as 1×10^{12} Rads (Si)/Sec, and return to normal operation within a few microseconds. Single Event Effect (SEE) testing of International Rectifier P-Channel RAD HARD HEXFETs has demonstrated virtual immunity to SEE failure. Since the P-Channel RAD HARD process utilizes International Rectifier's patented HEXFET technology, the user can expect the highest quality and reliability in the industry.

P-Channel RAD HARD HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits in space and weapons environments.

Product Summary

Part Number	BV_{DSS}	$R_{DS(on)}$	I_D
IRH9230	-200V	0.8 Ω	-6.5A

Features:

- Radiation Hardened up to 1×10^5 Rads (Si)
- Single Event Burnout (SEB) Hardened
- Single Event Gate Rupture (SEGR) Hardened
- Gamma Dot (Flash X-Ray) Hardened
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Absolute Maximum Ratings

Pre-Radiation

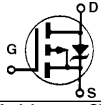
	Parameter	IRH9230	Units
I_D @ $V_{GS} = -12V$, $T_C = 25^\circ C$	Continuous Drain Current	-6.5	A
I_D @ $V_{GS} = -12V$, $T_C = 100^\circ C$	Continuous Drain Current	-4.1	
I_{DM}	Pulsed Drain Current ①	-26	
P_D @ $T_C = 25^\circ C$	Max. Power Dissipation	75	W
	Linear Derating Factor	0.2	W/K ⑤
V_{GS}	Gate-to-Source Voltage	± 20	V
EAS	Single Pulse Avalanche Energy ②	330	mJ
I_{AR}	Avalanche Current ①	-6.5	A
EAR	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction	-55 to 150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	11.5 (typical)	g

Notes: See page 4

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	-200	—	—	V	V _{GS} = 0V, I _D = 1.0 mA	
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	-0.10	—	V/°C	Reference to 25°C, I _D = -1.0 mA	
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.8	Ω	V _{GS} = -12V, I _D = -4.1A ④	
		—	—	0.92		V _{GS} = -12V, I _D = -6.5A	
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -1.0 mA	
g _{fs}	Forward Transconductance	2.5	—	—	S (㉑)	V _{DS} > -15V, I _{DS} = -6.5A ④	
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-25	μA	V _{DS} = 0.8 x Max. Rating, V _{GS} = 0V	
		—	—	-250		V _{DS} = 0.8 x Max. Rating V _{GS} = 0V, T _J = 125°C	
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V	
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100		V _{GS} = +20V	
Q _g	Total Gate Charge	—	—	35	nC	V _{GS} = -12V, I _D = -6.5A	
Q _{gs}	Gate-to-Source Charge	—	—	10		V _{DS} = Max. Rating x 0.5	
Q _{gd}	Gate-to-Drain (“Miller”) Charge	—	—	25			
t _{d(on)}	Turn-On Delay Time	—	—	50	ns	V _{DD} = -50V, I _D = -6.5A, R _G = 7.5Ω	
t _r	Rise Time	—	—	90			
t _{d(off)}	Turn-Off Delay Time	—	—	90			
t _f	Fall Time	—	—	90			
L _D	Internal Drain Inductance	—	5.0	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.	Modified MOSFET symbol showing the internal inductances. 
L _S	Internal Source Inductance	—	15	—		Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.	
C _{iss}	Input Capacitance	—	900	—	pF	V _{GS} = 0V, V _{DS} = -25V	
C _{oss}	Output Capacitance	—	250	—		f = 1.0 MHz	
C _{rss}	Reverse Transfer Capacitance	—	45	—			

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions		
IS	Continuous Source Current (Body Diode)	—	—	-6.5	A	Modified MOSFET symbol showing the integral Reverse p-n junction rectifier. 		
ISM	Pulse Source Current (Body Diode) ①	—	—	-26				
VSD	Diode Forward Voltage	—	—	-5.0	V		Tj = 25°C, IS = -6.5A, VGS = 0V ④	
trr	Reverse Recovery Time	—	—	400	ns			Tj = 25°C, IF = -6.5A, di/dt ≤ -100 A/μs VDD ≤ -14V ④
QRR	Reverse Recovery Charge	—	—	4.0	μC			
ton	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by LS + LD.						

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RthJC	Junction-to-Case	—	—	1.67	K/W ⑤	
RthJA	Junction-to-Ambient	—	30	—		

Radiation Performance of P-Channel Rad Hard HEXFETs

International Rectifier Radiation Hardened HEXFETs are tested to verify their hardness capability. The hardness assurance program at International Rectifier uses two radiation environments.

Every manufacturing lot is tested in a low dose rate (total dose) environment per MIL-STD-750, test method 1019. International Rectifier has imposed a standard gate voltage of -12 volts per note 6 and a VDSS bias condition equal to 80% of the device rated voltage per note 7. Pre- and post-radiation limits of the devices irradiated to 1×10^5 Rads (Si) are identical and are presented in Table 1. The values in Table 1 will be met for either of the two low dose rate test circuits that are used.

Both pre- and post-radiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison. It should be noted that at a radiation level of 1×10^5 Rads (Si), no change in limits are specified in DC parameters.

High dose rate testing may be done on a special request basis, using a dose rate up to 1×10^{12} Rads (Si)/Sec.

International Rectifier radiation hardened P-Channel HEXFETs are considered to be neutron-tolerant, as stated in MIL-PRF-19500 Group D. International Rectifier P-Channel radiation hardened HEXFETs have been characterized in heavy ion Single Event Effects environment and the results are shown in Table 3.

Table 1. Low Dose Rate ⑥ ⑦

Parameter		100K Rads (Si)		Units	Test Conditions ⑧
		min.	max.		
BVDSS	Drain-to-Source Breakdown Voltage	-200	—	V	$V_{GS} = 0V, I_D = -1.0 \text{ mA}$
VGS(th)	Gate Threshold Voltage ④	-2.0	-4.0		$V_{GS} = V_{DS}, I_D = -1.0 \text{ mA}$
IGSS	Gate-to-Source Leakage Forward	—	-100	nA	$V_{GS} = -20V$
IGSS	Gate-to-Source Leakage Reverse	—	100		$V_{GS} = 20V$
IDSS	Zero Gate Voltage Drain Current	—	-25	μA	$V_{DS} = 0.8 \times \text{Max Rating}, V_{GS} = 0V$
RDS(on)1	Static Drain-to-Source ④ On-State Resistance One	—	0.8	Ω	$V_{GS} = -12V, I_D = -4.1A$
VSD	Diode Forward Voltage ④	—	-5.0	V	$T_C = 25^\circ C, I_S = -6.5A, V_{GS} = 0V$

Table 2. High Dose Rate ⑧

Parameter		10 ¹¹ Rads (Si)/sec			10 ¹² Rads (Si)/sec			Units	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
VDSS	Drain-to-Source Voltage	—	—	-160	—	—	-160	V	Applied drain-to-source voltage during gamma-dot
Ipp		—	-12	—	—	-12	—	A	Peak radiation induced photo-current
di/dt		—	-160	—	—	-8	—	A/ μ sec	Rate of rise of photo-current
L1		1	—	—	20	—	—	μH	Circuit inductance required to limit di/dt

Table 3. Single Event Effects ⑨

Parameter	Typ.	Units	Ion	LET (Si) (MeV/mg/cm ²)	Fluence (ions / cm ²)	Range (μm)	VDS Bias (V)	VGS Bias (V)
BVDSS	-200	V	Ni	28	1×10^5	~41	-200	5

IRH9230 Device

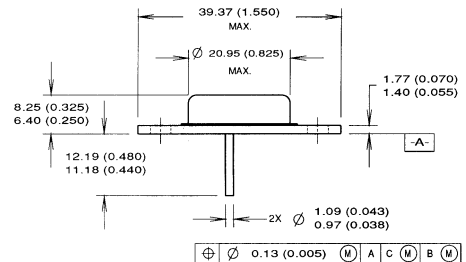
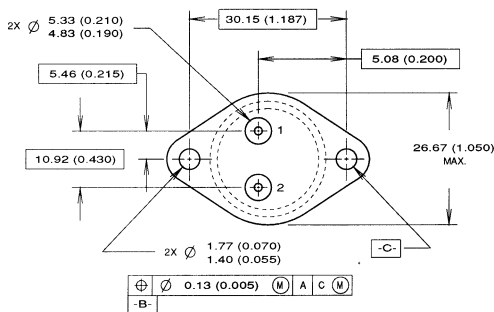
Radiation Characteristics

- ① **Repetitive Rating**; Pulse width limited by maximum junction temperature.
Refer to current HEXFET reliability report.
- ② @ $V_{DD} = 50V$, Starting $T_J = 25^\circ C$,
 $EAS = [0.5 * L * (I_L^2) * [BV_{DSS}/(BV_{DSS} - V_{DD})]]$
Peak $I_L = -6.5A$, $V_{GS} = -12V$, $25 \leq R_G \leq 200 \Omega$
- ③ $I_{SD} \leq -6.5A$, $di/dt \leq -140 A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
Suggested $R_G = 2.35 \Omega$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^\circ C/W$
 $W/K = W/^\circ C$
- ⑥ **Total Dose Irradiation with V_{GS} Bias.**
-12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑦ **Total Dose Irradiation with V_{DS} Bias.**
 $V_{DS} = 0.8$ rated BV_{DSS} (pre-radiation) applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑧ This test is performed using a flash x-ray source operated in the e-beam mode (energy ~ 2.5 MeV), 30 nsec pulse.
- ⑨ Process characterized by independent laboratory.
- ⑩ All Pre-Radiation and Post-Radiation test conditions are **identical** to facilitate direct comparison for circuit applications.

Case Outline and Dimensions

Conforms to JEDEC Outline TO-204AA (Modified TO-3)

Dimensions in Millimeters and (Inches)



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IR Rectifier

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Data and specifications subject to change without notice.

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